

General Description

The HSH8119 is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The HSH8119 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

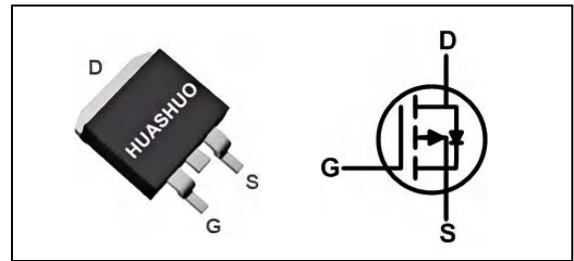
Product Summary

V_{DS}	-80	V
$R_{DS(ON),typ}$	13.5	m Ω
I_D	-90	A

Features

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

TO-263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-80	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-90	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-60	A
I_{DM}	Pulsed Drain Current ²	-270	A
EAS	Single Pulse Avalanche Energy ³	710	mJ
I_{AS}	Avalanche Current	63	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	210	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.73	$^\circ\text{C/W}$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-80	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-20A$	---	13.5	15	$m\Omega$
		$V_{GS}=-4.5V, I_D=-10A$	---	14.5	17	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.8	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-80V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-80V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1.0\text{MHz}$	---	1.7	---	Ω
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-3A$	---	30	---	S
Q_g	Total Gate Charge	$V_{DS}=-40V, V_{GS}=-10V, I_D=-10A$	---	190	---	nC
Q_{gs}	Gate-Source Charge		---	29	---	
Q_{gd}	Gate-Drain Charge		---	55	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-40V, V_{GS}=-10V, R_G=6\Omega, I_D=-10A$	---	25	---	ns
T_r	Rise Time		---	20	---	
$T_{d(off)}$	Turn-Off Delay Time		---	180	---	
T_f	Fall Time		---	88	---	
C_{iss}	Input Capacitance	$V_{DS}=-40V, V_{GS}=0V, f=1\text{MHz}$	---	13300	---	pF
C_{oss}	Output Capacitance		---	390	---	
C_{rss}	Reverse Transfer Capacitance		---	50	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-90	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-270	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V
T_{rr}	Reverse Recovery Time	$I_F=-20A, di/dt=100A/\mu s$	---	35	---	ns
Q_{rr}	Reverse Recovery Charge	$I_F=-20A, di/dt=100A/\mu s$	---	45	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

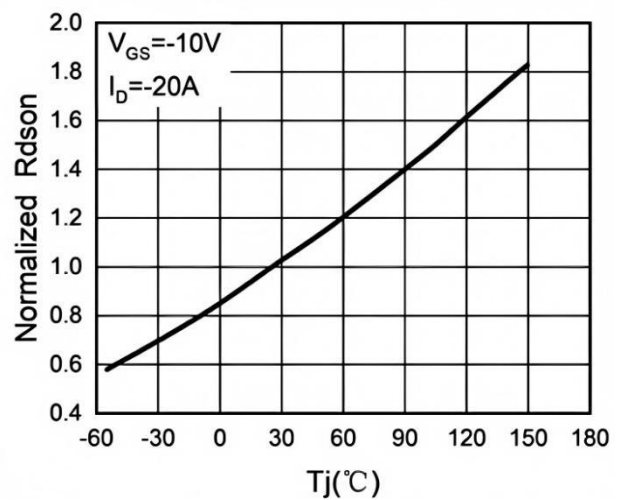
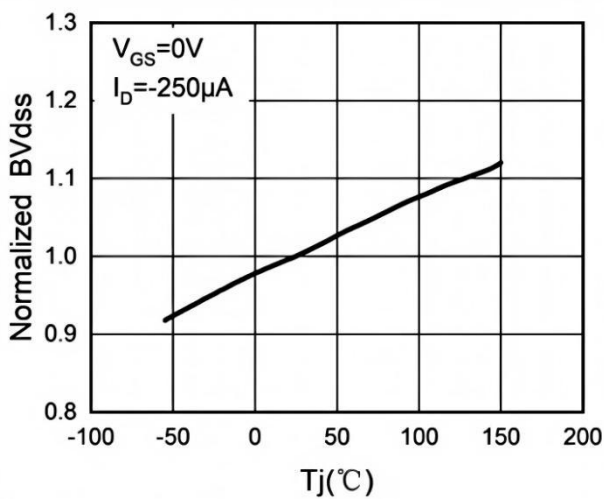
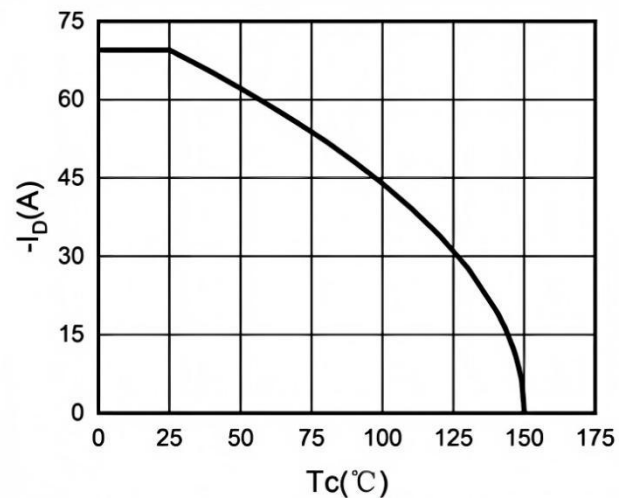
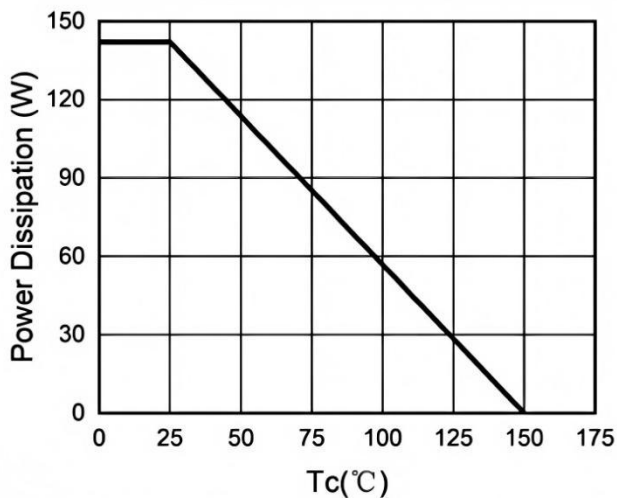
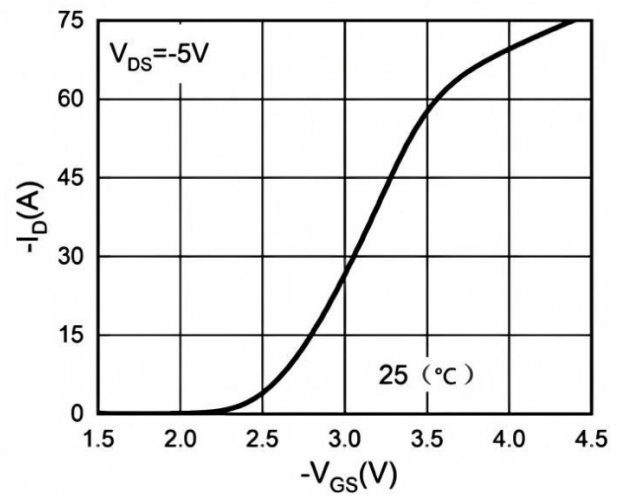
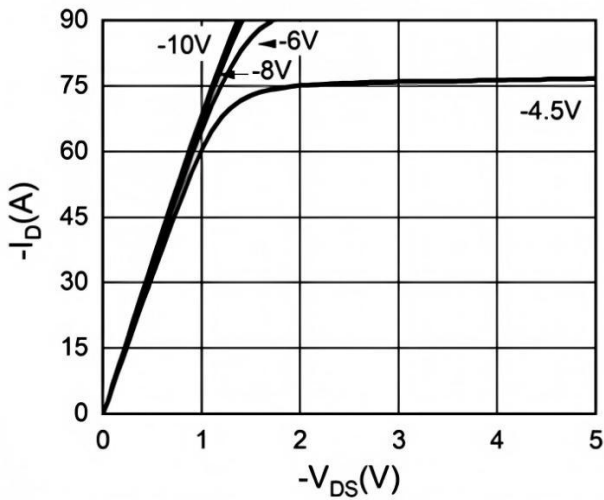
3. The EAS data shows Max. rating. The test condition is $V_{DD}=-50V, V_{GS}=-10V, L=0.1\text{mH}, R_g=25\Omega, I_{AS}=-63A$

4. The power dissipation is limited by 150°C junction temperature

5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics





P-Ch 80V Fast Switching MOSFETs

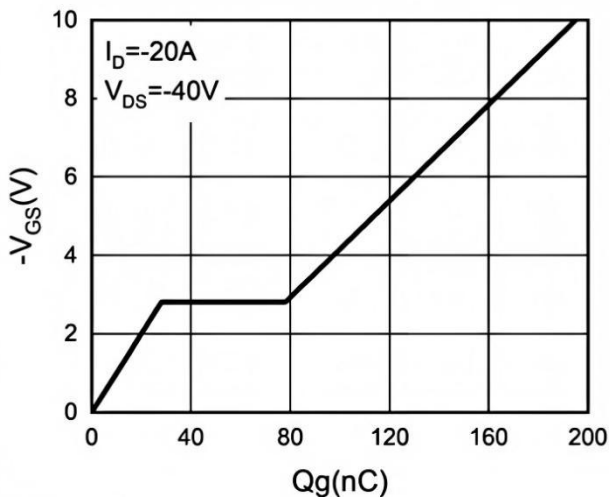


Fig.7 Gate Charge Waveforms

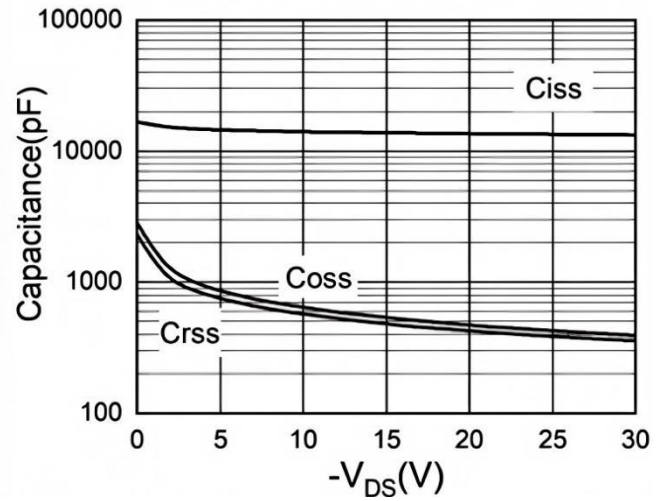


Fig.8 Capacitance

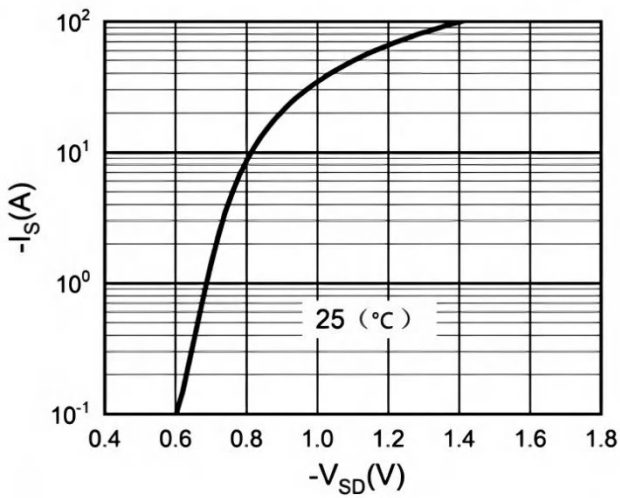


Fig.9 Body Diode Characteristics

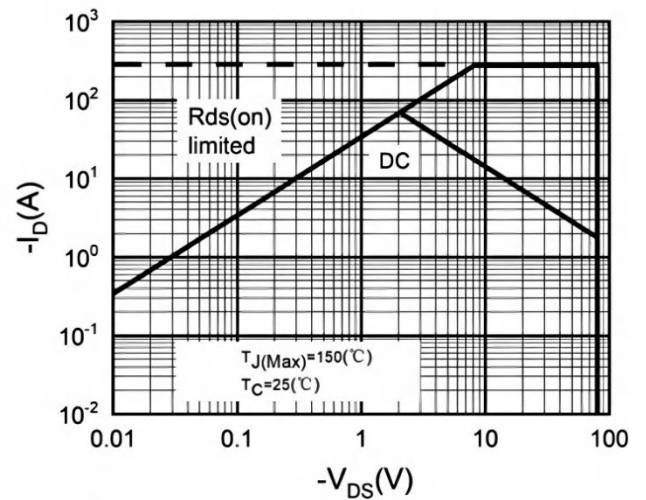


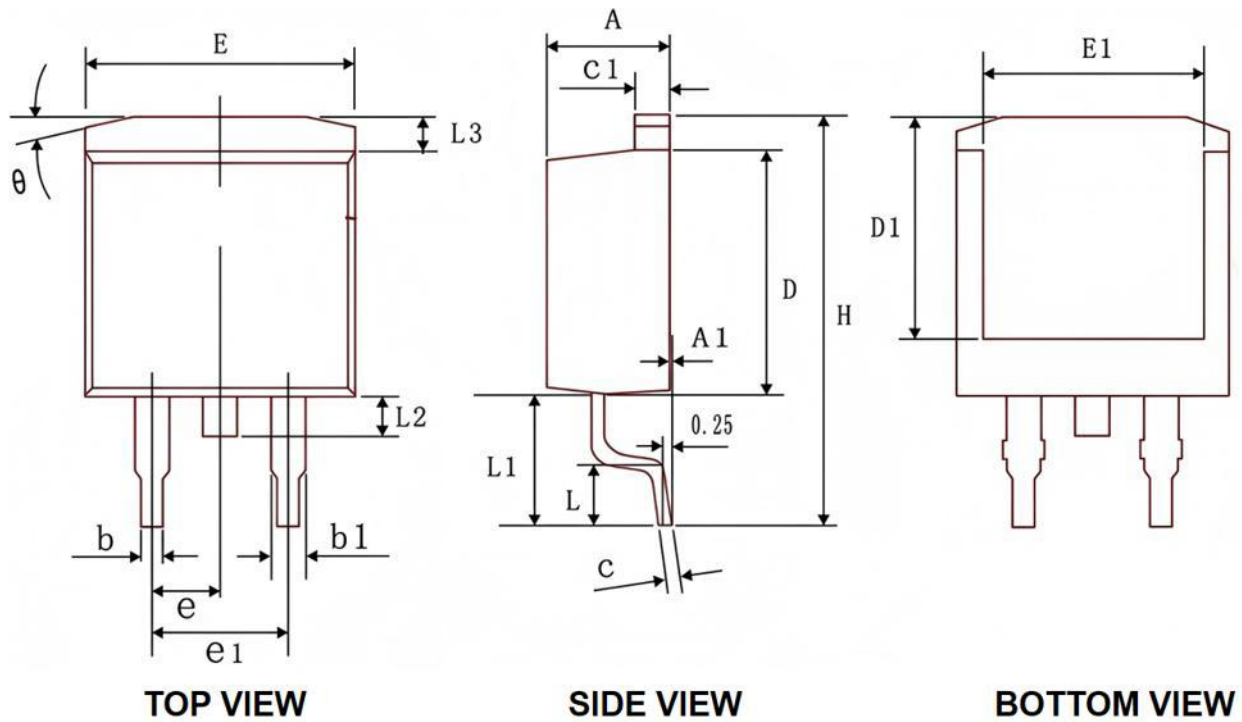
Fig.10 Maximum Safe Operating Area



Ordering Information

Part Number	Package code	Packaging
HSH8119	TO-263	800/Tape&Reel

TO-263 Package Outline



COMMON DIMENSIONS(UNIT OF MEASURE - MM)

SYMBOL	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	0.00	-	0.25
b	0.70	0.83	0.96
b1	1.00	1.24	1.47
C	0.35	0.45	0.55
C1	1.25	1.30	1.35
D	8.50	8.90	9.30
D1	7.50	8.00	8.50
H	14.7	15.20	15.7
E	9.80	10.08	10.4
E1	7.35	7.80	8.25
e1	4.93	5.08	5.23
L	2.00	2.30	2.60
L1	4.50	4.75	5.00
L2	1.30	1.53	1.75
L3	1.10	1.29	1.47
e	2.54 BSC		
θ	13°TYP		



HSH8119 Marking:

